

# MOSPEC

## MEDIUM-POWER COMPLEMENTARY SILICON TRANSISTORS

...designed for use as output devices in complementary general purpose amplifier applications.

### FEATURES:

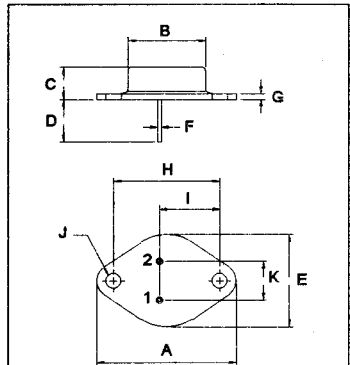
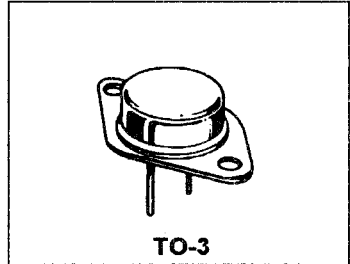
- \* High Gain Darlington Performance
- \* DC Current Gain  $hFE = 3500(\text{Typ}) @ I_C = 10 \text{ A}$
- \* Monolithic Construction with Built-in Base-Emitter Shunt Resistor

PNP	NPN
MJ4030	MJ4033
MJ4031	MJ4034
MJ4032	MJ4035

16 AMPERE  
COMPLEMENTARY  
SILICON POWER  
DARLINGTON TRANSISTOR  
60-100 VOLTS  
150 WATTS

### MAXIMUM RATINGS

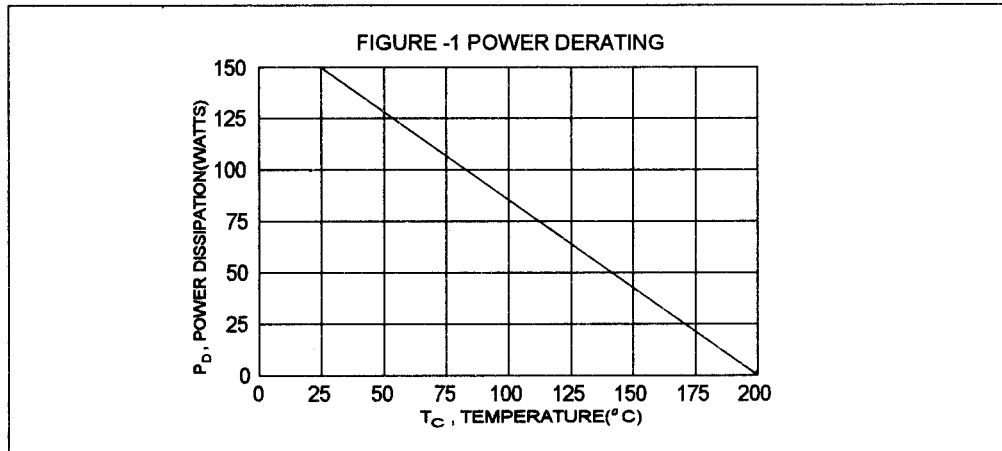
Characteristic	Symbol	MJ4030 MJ4033	MJ4031 MJ4034	MJ4032 MJ4035	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	100	V
Collector-Base Voltage	$V_{CBO}$	60	80	100	V
Emitter-Base Voltage	$V_{EBO}$	5.0			V
Collector Current-Continuous -Peak	$I_C$ $I_{CM}$	16 20			A
Base Current	$I_B$	0.5			A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	150 0.857			W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	- 65 to +200			$^\circ\text{C}$



PIN 1. BASE  
2. EMITTER  
COLLECTOR (CASE)

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.17	$^\circ\text{C/W}$



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

**MJ4030, MJ4031, MJ4032 PNP / MJ4033, MJ4034, MJ4035 NPN**

**ELECTRICAL CHARACTERISTICS (  $T_c = 25^\circ\text{C}$  unless otherwise noted )**

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

**OFF CHARACTERISTICS**

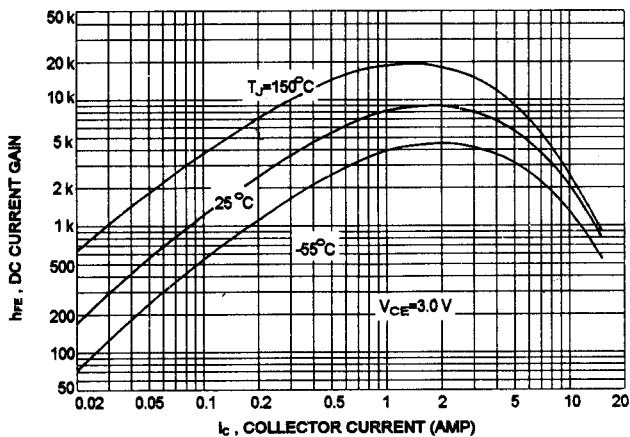
Collector - Emitter Sustaining Voltage (1) ( $I_c = 100\text{ mA}$ , $I_B = 0$ ) MJ4030,MJ4033 MJ4031,MJ4034 MJ4032,MJ4035	$V_{CE(sus)}$	60 80 100		V
Collector Cutoff Current ( $V_{CE} = 30\text{ V}$ , $I_B = 0$ ) ( $V_{CE} = 40\text{ V}$ , $I_B = 0$ ) ( $V_{CE} = 50\text{ V}$ , $I_B = 0$ ) MJ4030,MJ4033 MJ4031,MJ4034 MJ4032,MJ4035	$I_{CEO}$		3.0 3.0 3.0	mA
Collector-Emitter Leakage Current ( $V_{CE} = 60\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ ) ( $V_{CE} = 80\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ ) ( $V_{CE} = 100\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ ) ( $V_{CE} = 60\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ , $T_c = 150^\circ\text{C}$ ) ( $V_{CE} = 80\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ , $T_c = 150^\circ\text{C}$ ) ( $V_{CE} = 100\text{ V}$ , $R_{BE} = 1.0\text{k ohm}$ , $T_c = 150^\circ\text{C}$ ) MJ4030,MJ4033 MJ4031,MJ4034 MJ4032,MJ4035 MJ4030,MJ4033 MJ4031,MJ4034 MJ4032,MJ4035	$I_{CER}$		1.0 1.0 1.0 5.0 5.0 5.0	mA
Emitter Cutoff Current ( $V_{EB} = 5.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$		5.0	mA

**ON CHARACTERISTICS (1)**

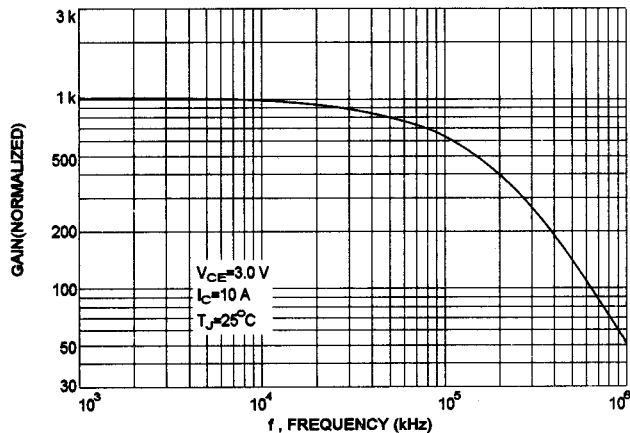
DC Current Gain ( $I_c = 10\text{ A}$ , $V_{CE} = 3.0\text{ V}$ )	hFE	1000		
Collector-Emitter Saturation Voltage ( $I_c = 10\text{ A}$ , $I_B = 40\text{ mA}$ ) ( $I_c = 16\text{ A}$ , $I_B = 80\text{ mA}$ )	$V_{CE(sat)}$		2.5 4.0	V
Base-Emitter On Voltage ( $I_c = 10\text{ A}$ , $V_{CE} = 3.0\text{ V}$ )	$V_{BE(on)}$		3.0	V

(1) Pulse Test: Pulse width = 300 us , Duty Cycle  $\leq 2.0\%$

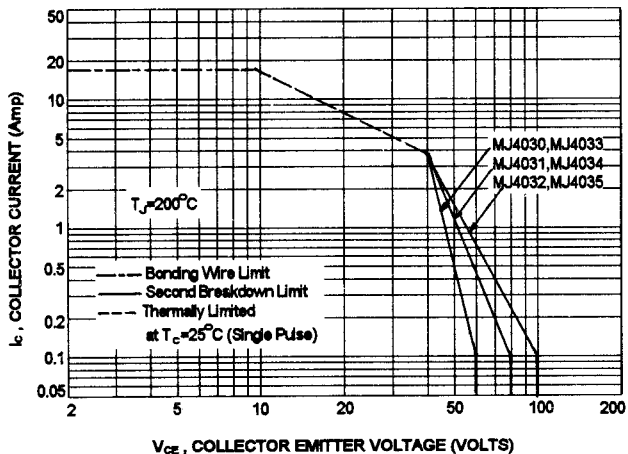
DC CURRENT GAIN



SMALL-SIGNAL CURRENT GAIN



ACTIVE-REGION SAFE OPERATING AREA (SOA)



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

At high temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

"ON" VOLTAGE

